In the Claims:

Please cancel claim 8, without prejudice, and amend claims 1 and 9-10 as follows:

1. (Currently amended) A magnetoresistive film comprising a multilayered film including: a pinned magnetic layer having magnetization whose direction is fixed; a nonmagnetic middle layer formed on the pinned magnetic layer; and a free magnetic layer formed on the middle layer and provided with magnetization whose direction changes in accordance with an external magnetic field, and indicating a magnitude of resistance in accordance with an angle formed by the magnetization direction of the pinned magnetic layer and the magnetization direction of the free magnetic layer,

wherein a copper oxide layer of an oxide including a copper element is formed directly on said free magnetic layer, or on the free magnetic layer via an oxide layer comprising a material fabricated by oxidation of a material constituting the free magnetic layer,

wherein the copper oxide layer causes specular reflection on, without applying a bias magnetic field to, an interface between the copper oxide layer and the free magnetic layer when the copper oxide layer is formed directly on the free magnetic layer, and

wherein the copper oxide layer causes specular reflection on, without applying a bias magnetic field to, an interface between the free magnetic layer and the oxide layer and

on the interface between the oxide layer and the copper oxide layer when the copper oxide layer is formed on the free magnetic layer via the oxide layer.

2. (Original) The magnetoresistive film according to claim 1 wherein said copper oxide layer has a thickness of 10 angstroms or more.

3. (Original) The magnetoresistive film according to claim 1 wherein said oxide layer has a thickness of 5 angstroms or more.

4. (Original) The magnetoresistive film according to claim 1 wherein a protective layer for protecting the copper oxide layer is formed on said copper oxide layer.

5. (Original) The magnetoresistive film according to claim 4 wherein said protective layer comprises an oxide.

6. (Original) The magnetoresistive film according to claim 5 wherein said protective layer comprises $Al_2O_3$ .

7. (Original) The magnetoresistive film according to claim 1 wherein said free magnetic layer has a thickness of 30 angstroms or less.

8. (Cancelled)

9. (Currently amended) A magnetoresistive head comprising a magnetoresistive film as a multilayered film including: a pinned magnetic layer having magnetization whose direction is fixed; a nonmagnetic middle layer formed on the pinned magnetic layer; and a free magnetic layer formed on the middle layer and provided with magnetization whose direction changes in accordance with an external magnetic field and indicating a magnitude of resistance in accordance with an angle formed by the magnetization direction of the pinned magnetic layer and the magnetization direction of the free magnetic layer, and detecting the magnitude of the resistance of the magnetoresistive film to detect a strength of the external magnetic field,

wherein a copper oxide layer of an oxide including a copper element is formed directly on said free magnetic layer, or on the free magnetic layer via an oxide layer comprising a material fabricated by oxidation of a material constituting the free magnetic layer,

wherein the copper oxide layer causes specular reflection on, without applying a bias magnetic field to, an interface between the copper oxide layer and the free magnetic layer when the copper oxide layer is formed directly on the free magnetic layer, and

wherein the copper oxide layer causes specular reflection on, without applying a bias magnetic field to, an interface between the free magnetic layer and the oxide layer and

on the interface between the oxide layer and the copper oxide layer when the copper oxide layer is formed on the free magnetic layer via the oxide layer.

10. (Currently amended) An information regeneration apparatus comprising a magnetic head, disposed in the vicinity of or in contact with a magnetic recording medium on which information is recorded by a magnetization direction, for detecting the magnetization direction of each point of the magnetic recording medium, and regenerating the information in accordance with the magnetization direction of each point of said magnetic recording medium detected by the magnetic head,

wherein said magnetic head comprises a magnetoresistive film as a multilayered film including: a pinned magnetic layer having magnetization whose direction is fixed; a nonmagnetic middle layer formed on the pinned magnetic layer; and a free magnetic layer formed on the middle layer and provided with magnetization whose direction changes in accordance with an external magnetic field, and indicating a magnitude of resistance in accordance with an angle formed by the magnetization direction of the pinned magnetic layer and the magnetization direction of the free magnetic layer, and detects the magnitude of the resistance of the magnetoresistive film to detect a strength of the external magnetic field, and

a copper oxide layer of an oxide including a copper element is formed directly on said free magnetic layer, or on the free magnetic layer via an oxide layer formed of a material fabricated by oxidation of a material constituting the free magnetic layer,

wherein the copper oxide layer causes specular reflection on, without applying a bias magnetic field to, an interface between the copper oxide layer and the free magnetic layer when the copper oxide layer is formed directly on the free magnetic layer, and

wherein the copper oxide layer causes specular reflection on, without applying a bias magnetic field to, an interface between the free magnetic layer and the oxide layer and on the interface between the oxide layer and the copper oxide layer when the copper oxide layer is formed on the free magnetic layer via the oxide layer.

11. (Original) A magnetoresistive film manufacture method for manufacturing a magnetoresistive film as a multilayered film including: a pinned magnetic layer having magnetization whose direction is fixed; a nonmagnetic middle layer formed on the pinned magnetic layer; and a free magnetic layer formed on the middle layer and provided with magnetization whose direction changes in accordance with an external magnetic field, and indicating a magnitude of resistance in accordance with an angle formed by the magnetization direction of the pinned magnetic layer and the magnetization direction of the free magnetic layer,

said method comprising:

a free magnetic material layer lamination step of laminating said middle layer, and subsequently laminating a free magnetic material layer including a material constituting said free magnetic layer on the middle layer;

a metal layer lamination step of laminating a metal layer comprising a metal on

the free magnetic material layer laminated in said free magnetic material layer lamination step; and

a plasma oxidation step of exposing the metal layer laminated by said metal layer lamination step to oxygen in a plasma state to oxidize the metal layer.

12. (Original) The magnetoresistive film manufacture method according to claim 11 wherein said plasma oxidation step comprises a step of oxidizing said metal layer, and a part of said free magnetic material layer on the side of the metal layer.

13. (Original) The magnetoresistive film manufacture method according to claim 11 wherein said plasma oxidation step is performed simultaneously with lamination of a new layer on said metal layer.

14. (Original) A magnetoresistive film manufacture method for manufacturing a magnetoresistive film as a multilayered film including: a pinned magnetic layer having magnetization whose direction is fixed; a nonmagnetic middle layer formed on the pinned magnetic layer; and a free magnetic layer formed on the middle layer and provided with magnetization whose direction changes in accordance with an external magnetic field, and indicating a magnitude of resistance in accordance with an angle formed by the magnetization direction of the pinned magnetic layer and the magnetization direction of the free magnetic layer,

said method comprising:

a free magnetic material layer lamination step of laminating a free magnetic material layer comprising a material constituting said free magnetic layer on said middle layer;

an oxidation control layer lamination step of laminating a predetermined oxidation control layer on the free magnetic material layer laminated in said free magnetic material layer lamination step; and

a plasma oxidation step of exposing the oxidation control layer laminated by said oxidation control layer lamination step to oxygen in a plasma state to oxidize said free magnetic material layer to a predetermined depth in a thickness direction from an oxidation control layer side through the oxidation control layer.